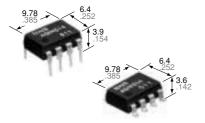
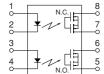


Compact DIP (1Form A/ 1Form B) 8-pin type. Controls load voltage 400V.

GU PhotoMOS (AQW614)



mm inch



FEATURES

1. Approx. 1/2 the space compared with the mounting of a set of 1 Form A and 1 Form B photoMOS relays 2. Applicable for 1 Form A 1 Form B

use as well as two independent 1 Form A and 1 Form B use

3. Low thermal electromotive force (Approx. 1 $\mu\text{V})$

4. Eliminates the need for a counter electromotive force protection diode in the drive circuits on the input side

5. Controls load currents up to 0.13 A with an input current of 5 mA with load voltage of 400 V

6. High speed switching: operate time of 300 μs typical.

7. Eliminates the need for a power supply to drive the power MOSFET

8. Extremely low closed-circuit offset voltages to enable control of small analog signals without distortion (Typical 100 pA at 400 V)

9. Stable on resistance

TYPICAL APPLICATIONS

· High-speed inspection machines

- Telephone equipment
- Computer

TYPES

Туре	Output rating*			Par				
	Load voltage	Load current	Through hole ter- minal	Surface-mount terminal			Packing quantity	
			Tube packing style		Tape and reel packing style			
					Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	Tube	Tape and reel
AC/DC type	400 V	100 mA	AQW614	AQW614A	AQW614AX	AQW614AZ	1 tube contains 40 pcs. 1 batch contains 400 pcs.	1,000 pcs.

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATINGS

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

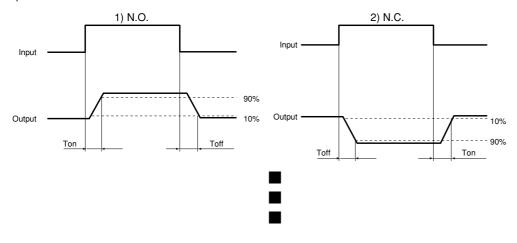
Item		Symbol	AQW614(A)	Remarks	
	LED forward current	IF	50 mA		
Input	LED reverse voltage	VR	5 V		
	Peak forward current	FP	1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin	75 mW		
	Load voltage	VL	400 V		
Output	Continuous load current	IL I	0.1 A (0.13 A)	Peak AC, DC (): in case of using only 1a or 1b, 1 channel	
	Peak load current	Ipeak	0.3 A	100 ms (1 shot), V∟ = DC	
	Power dissipation	Pout	800 mW		
Total power dissipation		Ρτ	850 mW		
I/O isolation voltage		Viso	1,500 V AC	Between input and output/between contact sets	
Tomporatura limit	Operating	Topr	−40°C to +85°C −40°F to +185°F	Non-condensing at low temperatures	
Temperature limit	s Storage	Tstg	-40°C to +100°C -40°F to +212°F		

GU PhotoMOS (AQW614)

aracteristics (Ambient tempe	rature: 25°C	; 77°F)		1	
Item		Symbol	AQW614(A)	Condition	
LED operate (OEE) current	Typical	IFon (N.O.)	0.9 mA	I∟ = 100 mA	
ELD operate (OFT) current	Maximum	IFoff (N.C.)	3 mA		
LED roverse (ON) ourrept	Minimum	IFoff (N.O.)	0.4 mA	lı = 100 mA	
LED reverse (ON) current	Typical	IFon (N.C.)	0.8 mA		
	Typical	Ve	1.25 V (1.14 V at I⊧ = 5 mA)	I⊧ = 50 mA	
LED dropout voltage	Maximum	VF	1.5 V	IF = 50 IIIA	
	Typical		27 Ω	$\label{eq:lf} \begin{array}{ c c c c c } I_{F} = 5 \mbox{ mA (N.O.)} \\ I_{F} = 0 \mbox{ mA (N.C.)} \\ I_{L} = 100 \mbox{ mA} \\ \mbox{ within 1 s on time} \end{array}$	
On resistance	Maximum	Ron	50 Ω		
Off state leakage current	Maximum	Leak	1 μΑ		
Operate (OEE) time*	Typical	Ton (N.O.)	0.28 ms (N.O.) 0.43 ms (N.C.)	I⊧ = 0 mA → 5 mA	
Operate (OFF) time	Maximum	Toff (N.C.)	1 ms	I∟ = 100 mA	
Deverse (ON) time*	Typical	Toff (N.O.)	0.04 ms (N.O.) 0.3 ms (N.C.)	I⊧ = 5 mA → 0 mA	
Reverse (ON) time	Maximum	Ton (N.C.)	1 ms	I∟ = 100 mA	
1/O conceitones	Typical	0	0.8 pF	f = 1 MHz V _B = 0 V	
	Maximum	Ciso	1.5 pF		
Initial I/O isolation resistance	Minimum	Riso	1,000 MΩ	500 V DC	
	Item LED operate (OFF) current LED reverse (ON) current LED dropout voltage On resistance Off state leakage current Operate (OFF) time* Reverse (ON) time* I/O capacitance	Item Typical LED operate (OFF) current Maximum LED reverse (ON) current Minimum Typical Typical LED dropout voltage Maximum On resistance Maximum Off state leakage current Maximum Operate (OFF) time* Typical Reverse (ON) time* Typical I/O capacitance Typical	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	

Note: Recommendable LED forward current IF = 5 mA.

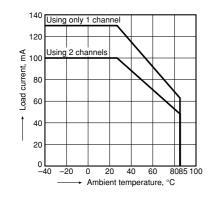
*Operate/Reverse time



REFERENCE DATA

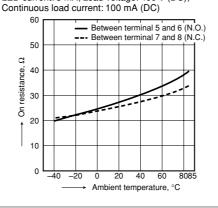
1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: –40°C to +85°C -40°F to +185°F



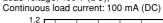
2. On resistance vs. ambient temperature characteristics

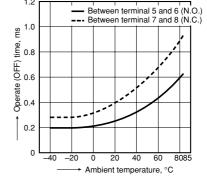
Measured portion: between terminals 5 and 6, 7 and 8; LED current: 5 mA; Load voltage: 400 V (DC);



3. Operate (OFF) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: 400 V (DC);



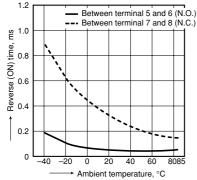


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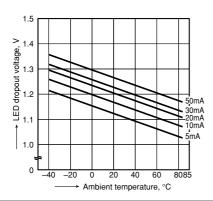
GU PhotoMOS (AQW614)

4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)

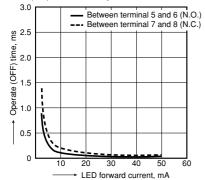


7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



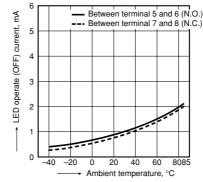
10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



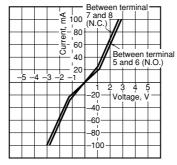
5. LED operate (OFF) current vs. ambient temperature characteristics Load voltage: 400 V (DC);

Continuous load current: 100 mA (DC)



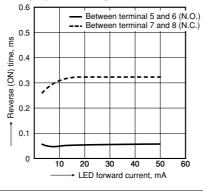
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8; Ambient temperature: $25^{\circ}C$ $77^{\circ}F$

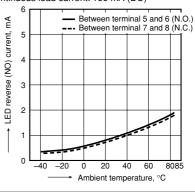


11. Reverse (ON) time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: $25^{\circ}C$ $77^{\circ}F$

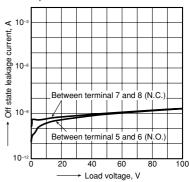


6. LED reverse (ON) current vs. ambient temperature characteristics Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Ambient temperature: $25^{\circ}C$ $77^{\circ}F$



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8; Frequency: 1 MHz;



